



# GaAs InGaP HBT MMIC POWER AMPLIFIER, 5.0 - 6.0 GHz

### **Typical Applications**

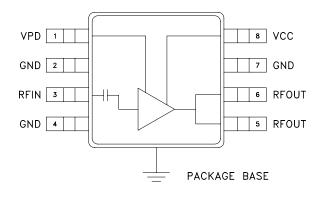
This amplifier is ideal for use as a driver amplifier for 5.0 - 6.0 GHz applications:

- UNII
- HiperLAN & 802.11a WLAN

#### Features

Gain: 17 dB Saturated Power: +29 dBm 38% PAE Supply Voltage: +5.0 V Power Down Capability Low External Part Count

### Functional Diagram



### **General Description**

The HMC406MS8G & HMC406MS8GE are high efficiency GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC Power amplifiers which operate between 5.0 and 6.0 GHz. The amplifier is packaged in a low cost, surface mount 8 leaded package with an exposed base for improved RF and thermal performance. With a minimum of external components, the amplifier provides 17 dB of gain and +29 dBm of saturated power at 38% PAE from a +5.0V supply voltage. Vpd can be used for full power down or RF output power/current control.

### Electrical Specifications, $T_A = +25^{\circ} C$ , Vs = 5V, Vpd = 5V

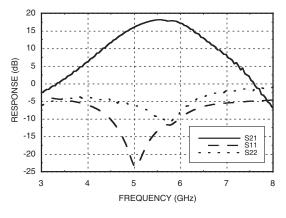
Parameter		Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range			5.0 - 6.0			5.7 - 5.9		GHz
Gain		13	16	21	14	17	21	dB
Gain Variation Over Temperature			0.03	0.04		0.03	0.04	dB/ °C
Input Return Loss			10			11		dB
Output Return Loss			8			9		dB
Output Power for 1 dB Compression (P1dB)		21	24		24	27		dBm
Saturated Output Power (Psat)			27			29		dBm
Output Third Order Intercept (IP3)		34	38		34	38		dBm
Noise Figure			6.0			6.0		dB
Supply Current (Icq)	Vpd = 0V/5V		0.002 / 300			0.002 / 300		mA
Control Current (Ipd)	Vpd = 5V		7			7		mA
Switching Speed	tON, tOFF		35			35		ns

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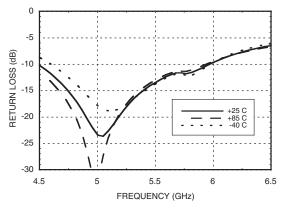


# ROHS EARTH FRIENDL

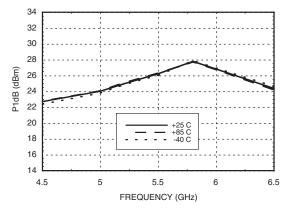
#### Broadband Gain & Return Loss



Input Return Loss vs. Temperature

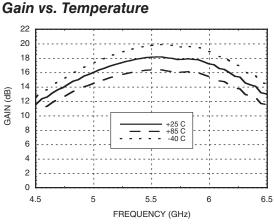


P1dB vs. Temperature

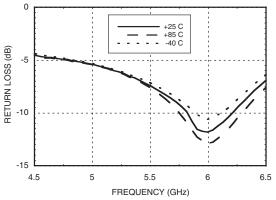


# HMC406MS8G / 406MS8GE

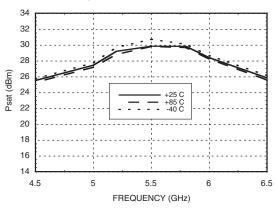
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#### Output Return Loss vs. Temperature







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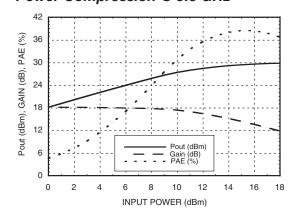
**AMPLIFIERS - SMT** 

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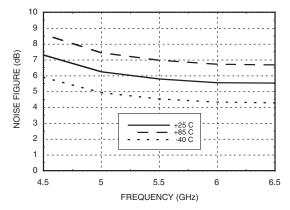




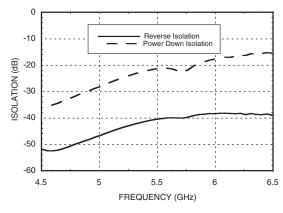
# Power Compression @ 5.8 GHz



#### Noise Figure vs. Temperature

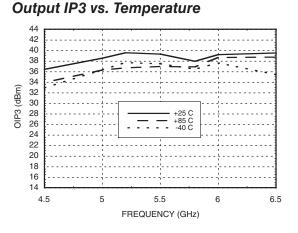


#### **Reverse Isolation vs. Temperature**

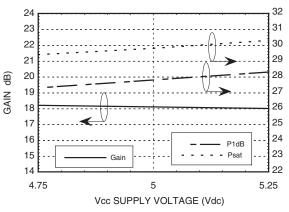


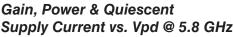
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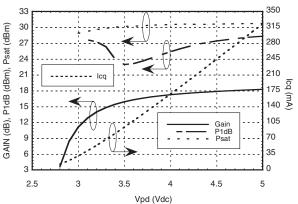
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#### Gain & Power vs. Supply Voltage







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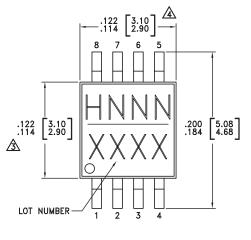
### Absolute Maximum Ratings

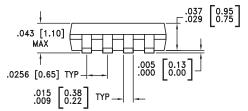
Collector Bias Voltage (Vcc)	+5.5 Vdc
Control Voltage (Vpd)	+5.5 Vdc
RF Input Power (RFin)(Vs = Vpd = +5.0 Vdc)	+20 dBm
Junction Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 32 mW/°C above 85 °C)	2.1 W
Thermal Resistance (junction to ground paddle)	31 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85° C



ELECTROSTATIC SENSITIVE DEVICE **OBSERVE HANDLING PRECAUTIONS** 

### **Outline Drawing**





.031 0.80 .070 [1.78] MĂX EXPOSED GROUND PADDLE .009 0.22 .003 0.08 .095 [2.41] MĀX

- NOTES:
- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.

A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE. 5. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC406MS8G	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H406 XXXX
HMC406MS8GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[2]</sup>	<u>H406</u> XXXX

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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# ROHS V EARTH FRIENDLY

### GaAs InGaP HBT MMIC POWER AMPLIFIER, 5.0 - 6.0 GHz

### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1	Vpd	Power Control Pin. For maximum power, this pin should be connected to 5.0V. A higher voltage is not recommended. For lower idle current, this voltage can be reduced.	OVPD
2, 4, 7	GND	Ground: Backside of package has exposed metal ground slug that must be connected to ground thru a short path. Vias under the device are required.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms from 5.5 to 6.0 GHz.	
5, 6	RFOUT	RF output and bias for the output stage. The power supply for the output device needs to be supplied to these pins.	ORFOUT
8	Vcc	Power supply voltage for the first amplifier stage. An exter- nal bypass capacitor of 330 pF is required. This capacitor should be placed as close to the devices as possible.	ovcc

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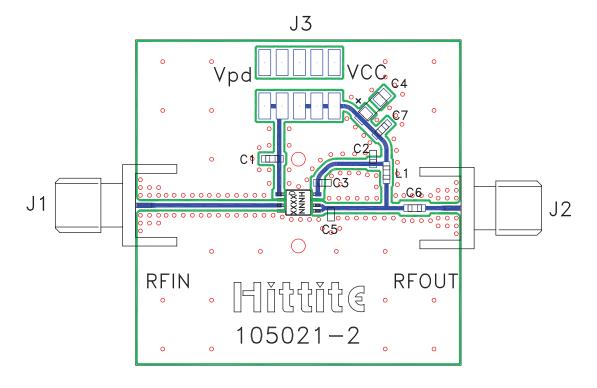
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# GaAs InGaP HBT MMIC POWER AMPLIFIER, 5.0 - 6.0 GHz



### **Evaluation PCB**



#### List of Materials for Evaluation PCB 104989<sup>[1]</sup>

Item	Description		
J1 - J2	PCB Mount SMA RF Connector		
J3	2mm DC Header		
C1 - C3	330 pF Capacitor, 0603 Pkg.		
C4	2.2 µF Capacitor, Tantalum		
C5	0.6 pF Capacitor, 0603 Pkg.		
C6	1.6 pF Capacitor, 0603 Pkg.		
C7	100 pF Capacitor, 0603 Pkg.		
L1	3.9 nH Inductor, 0603 Pkg.		
U1	HMC406MS8G / HMC406MS8GE Amplifier		
PCB <sup>[2]</sup>	105021 Eval Board		

Reference this number when ordering complete evaluation PCB
Circuit Board Material: Roger 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request. AMPLIFIERS - SMT

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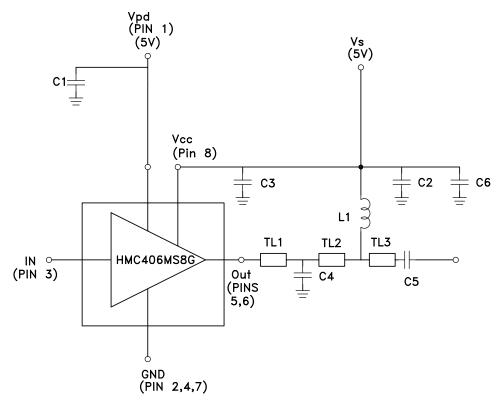


## GaAs InGaP HBT MMIC POWER AMPLIFIER, 5.0 - 6.0 GHz



#### **Application Circuit**





Note 1: C3 should be located < 0.020" from Pin 8 (Vcc) Note 2: C2 should be located < 0.020" from L1.

	TL1	TL2	TL3
Impedance	50 Ohm	50 Ohm	50 Ohm
Length	0.038"	0.231"	0.1"

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ROHS V

# HMC406MS8G / 406MS8GE

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Notes:

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